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RD01MUS1T113 UHF Power Transistor for Radios TK-2170/3170 Transistor de Potencia

TK-2170

PARTS LIST

TX-RX UNIT (X57-7000-XX)

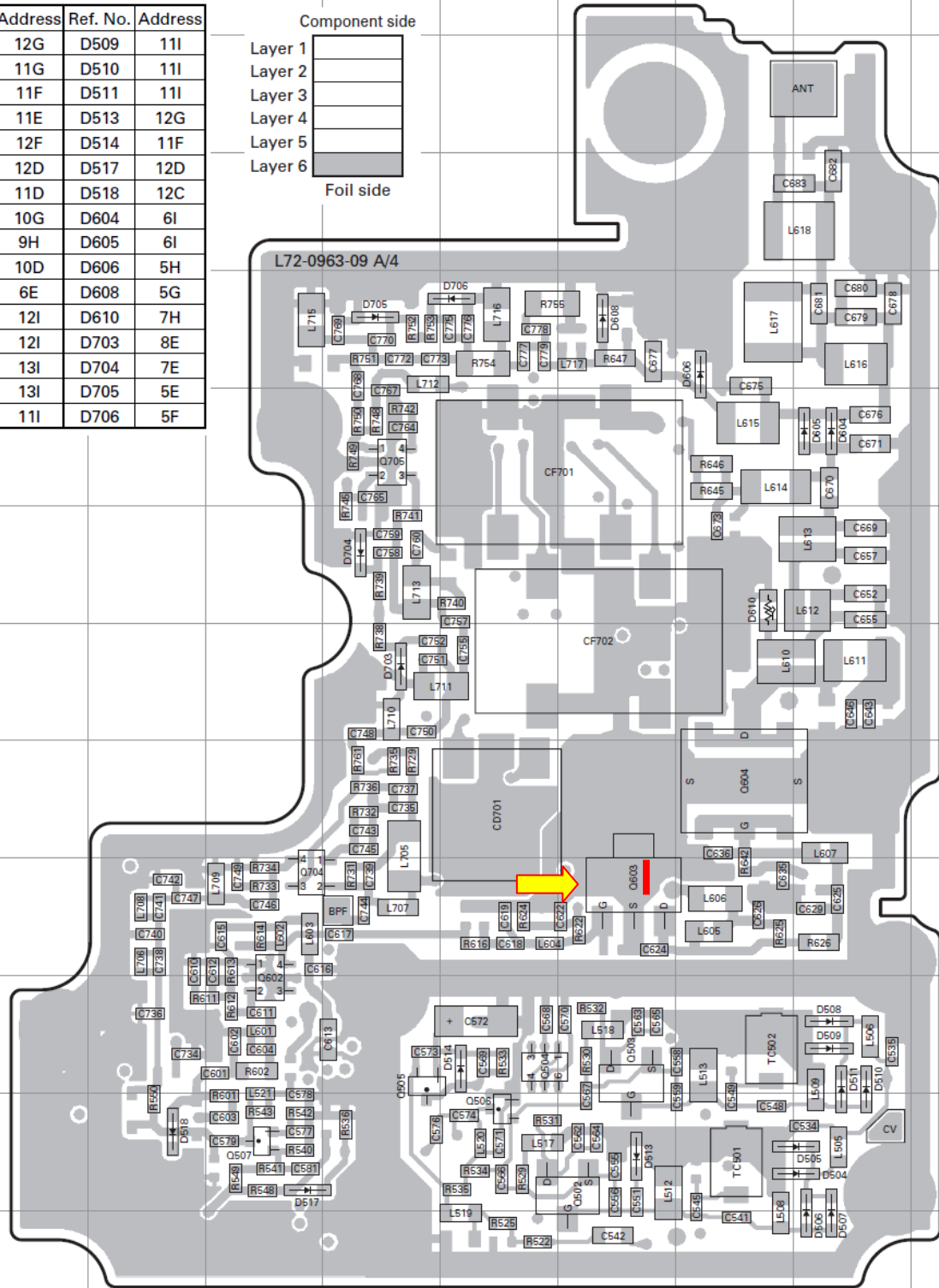
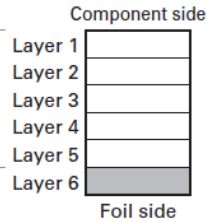
Ref. No.	Address	New parts	Parts No.	Description	Desti-nation	Ref. No.	Address	New parts	Parts No.	Description
Q6			UMG3N	TRANSISTOR						
Q7			UPA672T	FET						
Q8			DTA114EE	DIGITAL TRANSISTOR						
Q9		*	SSM6J08FU(F)	FET						
Q12			2SC4617(S)	TRANSISTOR						
Q13			2SB1132(Q,R)	TRANSISTOR						
Q14,15		*	SSM3K15TE(F)	FET						
Q16			2SA1774(S)	TRANSISTOR						
Q17			2SC4649(N,P)	TRANSISTOR						
Q19		*	SSM3K15TE(F)	FET						
Q21		*	RN4910(F)	TRANSISTOR						
Q22		*	SSM3K15TE(F)	FET						
Q23			DTC144EE	DIGITAL TRANSISTOR						
Q24		*	SSM6J08FU(F)	FET						
Q25		*	2SK1830F	FET						
Q26		*	2SJ347F	FET						
Q27			DTC144EE	DIGITAL TRANSISTOR						
Q28		*	SSM3K01T(F)	FET						
Q29		*	SSM3K15TE(F)	FET						
Q30			2S.J243	FET						
Q31,32			2SC4649(N,P)	TRANSISTOR						
Q33		*	2SJ347F	FET						
Q34		*	SSM3K15TE(F)	FET						
Q35		*	SSM3K01T(F)	FET						
Q501			2SC5488	TRANSISTOR						
Q502,503			2SK508NV(K52)	FET						
Q504		*	SSM6P05FU(F)	FET						
Q505			2SC4617(S)	TRANSISTOR						
Q506,507			2SC5488	TRANSISTOR						
Q602		*	2SK3077F	FET						
Q603			RD01MUS1	FET						
Q604			RD07MVS1	FET						
Q605			DTC114EE	DIGITAL TRANSISTOR						
Q607			DTC114EE	DIGITAL TRANSISTOR						
Q608			DTA144EE	DIGITAL TRANSISTOR						



PC BOARD TK-2170

TX-RX UNIT (X57-7000-XX) (A/4) -10 : K -11 : K2
Foil side view (J72-0963-09 A/4)

Ref. No.	Address	Ref. No.	Address
Q502	12G	D509	11I
Q503	11G	D510	11I
Q504	11F	D511	11I
Q505	11E	D513	12G
Q506	12F	D514	11F
Q507	12D	D517	12D
Q602	11D	D518	12C
Q603	10G	D604	6I
Q604	9H	D605	6I
Q704	10D	D606	5H
Q705	6E	D608	5G
D504	12I	D610	7H
D505	12I	D703	8E
D506	13I	D704	7E
D507	13I	D705	5E
D508	11I	D706	5F



< Silicon RF Power MOS FET (Discrete) >

RD01MUS1

RoHS Compliance, Silicon MOSFET Power Transistor 520MHz,1W

DESCRIPTION

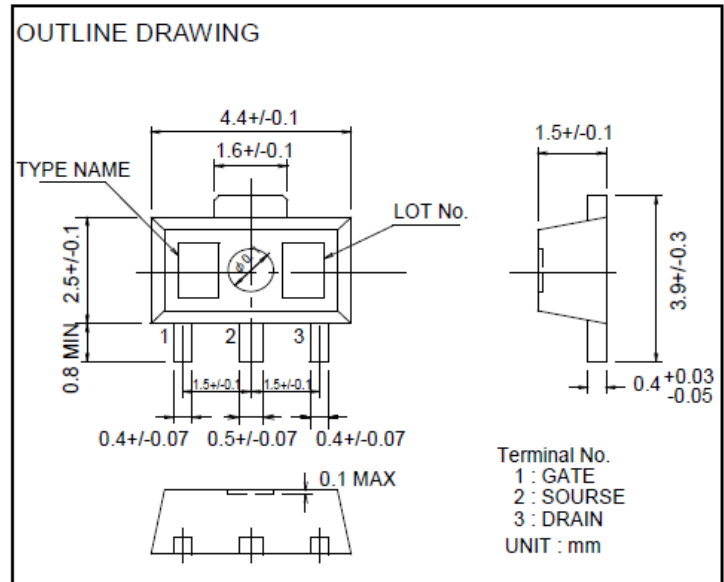
RD01MUS1 is a MOS FET type transistor specifically designed for VHF/UHF RF amplifiers applications.

FEATURES

High power gain:
 $P_{out} > 0.8W$, $G_p > 14dB$ @ $V_{dd} = 7.2V, f = 520MHz$
 High Efficiency: 65%typ.

APPLICATION

For output stage of high power amplifiers in VHF/UHF Band mobile radio sets.



RoHS COMPLIANT

RD01MUS1-101,T113 is a RoHS compliant products.

This product include the lead in high melting temperature type solders.

However, It is applicable to the following exceptions of RoHS Directions.

1. Lead in high melting temperature type solders (i.e. tin-lead solder alloys containing more than 85% lead.)

ABSOLUTE MAXIMUM RATINGS (Tc=25°C UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	RATINGS	UNIT
VDSS	Drain to source voltage	Vgs=0V	30	V
VGSS	Gate to source voltage	Vds=0V	+/-10	V
Pch	Channel dissipation	Tc=25°C	3.6	W
Pin	Input Power	Zg=Zl=50Ω	100	mW
ID	Drain Current	-	600	mA
Tch	Channel Temperature	-	150	°C
Tstg	Storage temperature	-	-40 to +125	°C
Rth j-c	Thermal resistance	Junction to case	34.5	°C/W

Note: Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
IDSS	Zero gate voltage drain current	VDS=17V, VGS=0V	-	-	50	uA
IGSS	Gate to source leak current	VGS=10V, VDS=0V	-	-	1	uA
Vth	Gate threshold Voltage	VDS=12V, IDS=1mA	1.3	1.8	2.3	V
Pout	Output power	VDD=7.2V, Pin=30mW	0.8	1.4	-	W
ηD	Drain efficiency	f=520MHz, Idq=100mA	50	65	-	%

Note: Above parameters, ratings, limits and conditions are subject to change.